# **BLF7G20L-250P**; **BLF7G20LS-250P**

**Power LDMOS transistor** 

Rev. 4 — 12 July 2013

**Product data sheet** 

## 1. Product profile

## 1.1 General description

250 W LDMOS power transistor for base station applications at frequencies from 1805 MHz to 1880 MHz.

Table 1. Typical performance

Typical RF performance at  $T_{\text{case}}$  = 25 °C in a common source class-AB production test circuit.

Mode of operation	f	$I_{Dq}$	$V_{DS}$	$P_{L(AV)}$	$G_p$	$\eta_D$	ACPR
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	1805 to 1880	1900	28	70	18	35	-29.5 <mark>[1]</mark>

<sup>[1]</sup> Test signal: 3GPP; test model 1;64 DPCH; PAR = 8.4 dB at 0.01% probability on CCDF.

#### 1.2 Features and benefits

- Excellent ruggedness
- High-efficiency
- Low R<sub>th</sub> providing excellent thermal stability
- Designed for broadband operation (1805 MHz to 1880 MHz)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

## 1.3 Applications

RF power amplifiers for W-CDMA base stations and multicarrier applications in the 1805 MHz to 1880 MHz frequency range



## 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified or	utline Grap	ohic symbol
BLF7G20	L-250P (SOT539A)			
1	drain1			
2	drain2	1 2	: 	1 . 🔟
3	gate1		5	3
4	gate2	3 4		5
5	source	<u>[1]</u>		4
				<b>'</b>
				2 sym117
				Syllilli

BLF7G	20LS-250P (SOT539B)	
1	drain1	
2	drain2	
3	gate1	5
4	gate2	3 4
5	source	<u>[1]</u>

<sup>[1]</sup> Connected to flange.

## 3. Ordering information

Table 3. Ordering information

	<u> </u>						
Type number	Packag	ge					
	Name	Description	Version				
BLF7G20L-250P	-	flanged balanced LDMOST ceramic package; 2 mounting holes; 4 leads	SOT539A				
BLF7G20LS-250P	-	earless flanged balanced LDMOST ceramic package; 4 leads	SOT539B				

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-0.5	+13	V
$I_D$	drain current		-	65	Α
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		-	200	°C

BLF7G20L-250P\_7G20LS-250P

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## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$\begin{aligned} &T_{case} = 80~^{\circ}\text{C};  P_L = 70~\text{W};  V_{DS} = 28~\text{V}; \\ &I_{Dq} = 1900~\text{mA};  T_j \leq 150~^{\circ}\text{C} \end{aligned}$	0.20	K/W

## 6. Characteristics

#### Table 6. Characteristics

 $T_i = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.5 \text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_{D} = 150 \text{ mA}$	1.5	1.78	2.3	V
I <sub>DSS</sub>	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$	-	-	2.8	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	33.4	37.54	Α
$I_{GSS}$	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	68.3	-	nA
9 <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 7.5 \text{ A}$	-	12.37	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 5.25 \text{ A}$	-	0.078	0.135	Ω

## 7. Test information

#### Table 7. 2-carrier W-CDMA functional test information

Class-AB production test circuit; PAR = 8.4 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 64 DPCH; f = 1805 MHz to 1880 MHz; RF performance at  $V_{DS} = 28$  V;  $I_{Dq} = 1900$  mA;  $T_{case} = 25$  °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$P_{L(AV)}$	average output power		-	70	-	W
Gp	power gain	$P_{L(AV)} = 70 \text{ W}$	16	18	-	dB
RLin	input return loss	$P_{L(AV)} = 70 \text{ W}$	-	-12	-	dB
$\eta_{D}$	drain efficiency	$P_{L(AV)} = 70 \text{ W}$	30	35	-	%
ACPR	adjacent channel power ratio	$P_{L(AV)} = 70 \text{ W}$	-	-29.5	-24.5	dBc

## 7.1 Ruggedness in class-AB operation

The BLF7G20L-250P and BLF7G20LS-250P are capable of withstanding a load mismatch corresponding to a VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS} = 28 \text{ V}$ ;  $I_{Dq} = 1900 \text{ mA}$ ;  $P_{L(1dB)} = 245 \text{ W}$  (CW); f = 1805 MHz to 1880 MHz.

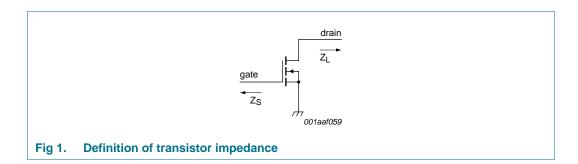
## 7.2 Impedance information

Table 8. Typical impedance

Measured load-pull data half device;  $I_{Dq} = 950$  mA;  $V_{DS} = 28$  V.

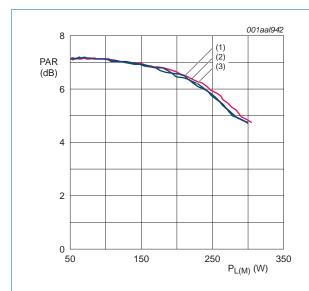
f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]
(MHz)	(Ω)	(Ω)
1750	1.31 – j3.53	2.47 – j3.91
1805	1.39 – j3.75	2.27 – j3.63
1845	1.48 – j4.10	2.32 – j3.19
1880	1.55 – j4.19	1.89 – j3.15
1930	1.97 – j4.48	1.70 – j2.95

[1]  $Z_S$  and  $Z_L$  defined in Figure 1.



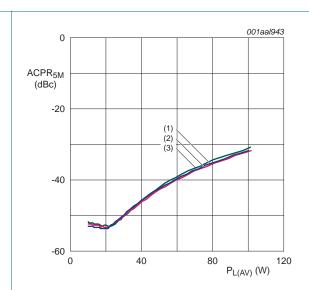
## 7.3 Single carrier W-CDMA

3GPP; test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF. Channel bandwidth is 3.84 MHz; channel spacing = 5 MHz;  $V_{DS}$  = 28 V;  $I_{Dg}$  = 1900 mA



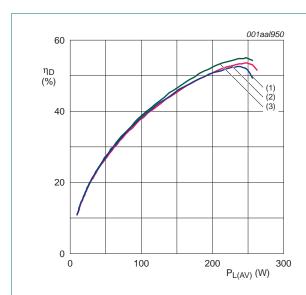
- (1) f = 1805 MHz.
- (2) f = 1845 MHz.
- (3) f = 1880 MHz.

Fig 2. Peak-to-average power ratio as a function of peak output power; typical values



- (1) f = 1805 MHz.
- (2) f = 1845 MHz.
- (3) f = 1880 MHz.

Fig 3. Adjacent channel power ratio (5 MHz) as a function of average output power; typical values



- (1) f = 1805 MHz.
- (2) f = 1845 MHz.
- (3) f = 1880 MHz.

Fig 4. Efficiency as a function of average output power; typical values

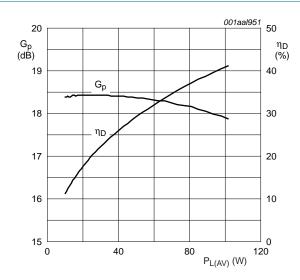
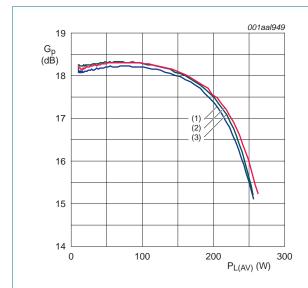


Fig 5. Power gain and drain efficiency as a function of average output power; typical values

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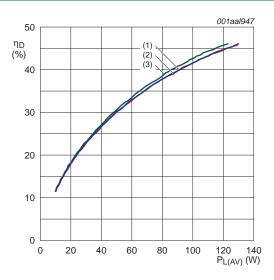
## 7.4 One tone CW

 $V_{DS} = 28 \text{ V}; I_{Dq} = 1900 \text{ mA}.$ 



- (1) f = 1805 MHz.
- (2) f = 1845 MHz.
- (3) f = 1880 MHz.

Fig 6. Power gain as a function of average output power; typical values

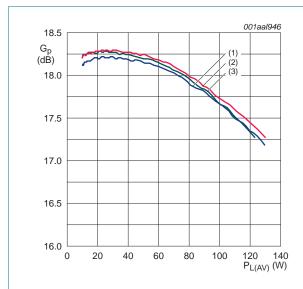


- (1) f = 1805 MHz.
- (2) f = 1845 MHz.
- (3) f = 1880 MHz.

Fig 7. Efficiency as a function of average output power; typical values

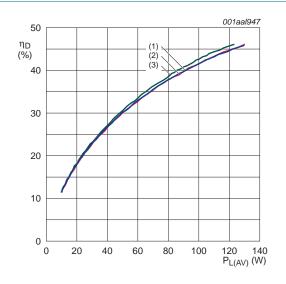
## 7.5 2-carrier WCDMA characteristics

 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1900 mA; channel spacing = 5 MHz; PAR = 8.4 dB at 0.01 % probability on the CCDF.



- (1) f = 1805 MHz.
- (2) f = 1845 MHz.
- (3) f = 1880 MHz.

Fig 8. Power gain as a function of average output power; typical values



- (1) f = 1805 MHz.
- (2) f = 1845 MHz.
- (3) f = 1880 MHz.

Fig 9. Efficiency as a function of average output power; typical values

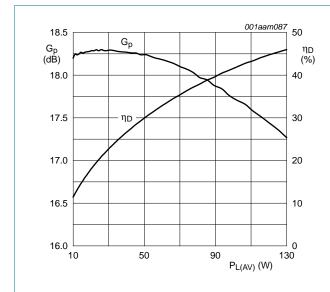
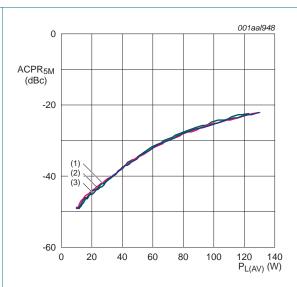


Fig 10. Average power gain and drain efficiency as a function of average output power; typical values



- (1) f = 1805 MHz.
- (2) f = 1845 MHz.
- (3) f = 1880 MHz.

Fig 11. Adjacent channel power ratio (5 MHz) as a function of average output power; typical values

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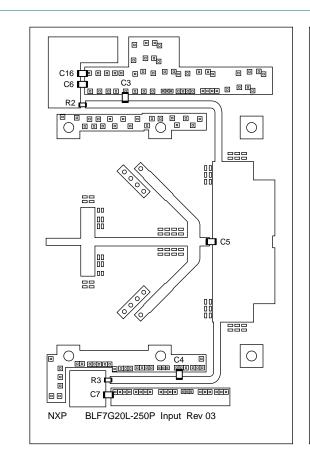
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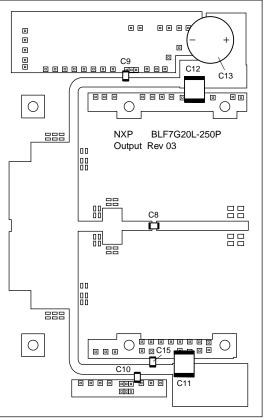
## 7.6 Test circuit

**Table 9.** List of components For test circuit see Figure 12.

Component	Description	Value	Code number	Туре	Remarks
Base plate [1	<u>1</u>				
C3, C4, C9, C10	multi layer ceramic chip capacitor	47 pF		ATC 800B	mount on edge
C5	multi layer ceramic chip capacitor	1.2 pF		ATC 800B	mount on edge
C6, C7	chip capacitor	560 pF		ATC 100A	
C8	multi layer ceramic chip capacitor	68 pF		ATC 800B	mount on edge
C11, C12	multi layer ceramic chip capacitor	10 μF		TDK	
C13	electrolytic capacitor	470 μF; 63 V			
C15, C16	multi layer ceramic chip capacitor	100 nF		Phillips 1206	
R2, R3	chip resistor	10 Ω		Philips 0603	

[1] See mechanical drawing (Figure 12).





Printed-Circuit Board (PCB): Taconic RF35;  $\epsilon r$  = 3.5 F/m; thickness = 0.76 mm; thickness copper plating = 35  $\mu$ m See Table 9 for a list of components.

Fig 12. Component layout for class-AB production test circuit

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## 8. Package outline

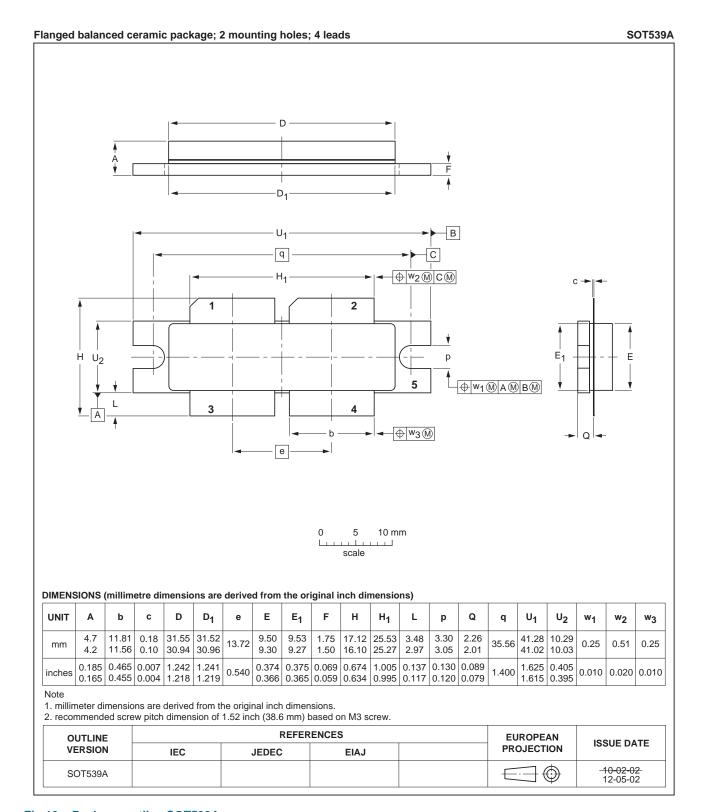


Fig 13. Package outline SOT539A

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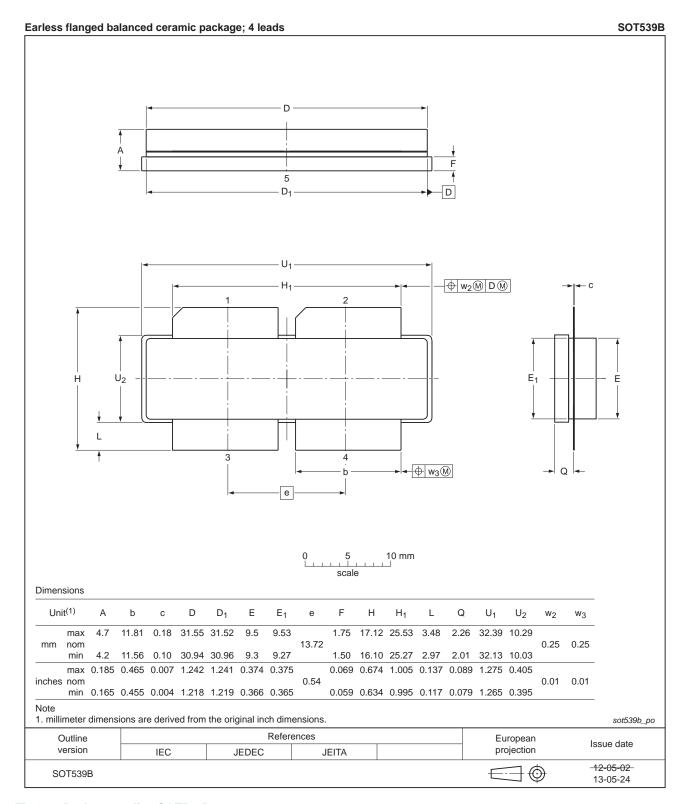


Fig 14. Package outline SOT539B

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## 9. Handling information

## CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

## 10. Abbreviations

Table 10. Abbreviations

Acronym	Description
3GPP	Third Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor
PAR	Peak-to-Average power Ratio
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

## 11. Revision history

## Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF7G20L-250P_7G20LS-250P v.4	20130712	Product data sheet	-	BLF7G20L-250P_7G20LS-250P v.3
Modifications:	<ul><li>The pa</li></ul>	ckage outline Figure 14	is updated.	
	<ul> <li>Transla</li> </ul>	tion disclaimer added to	the legal to	ext.
BLF7G20L-250P_7G20LS-250P v.3	20110103	Product data sheet	-	BLF7G20L-250P_7G20LS-250P v.2
Modifications:	<ul> <li>Data sh</li> </ul>	neet status changed from	n Prelimina	ry sheet to Product data sheet
	<ul><li>Table 1</li></ul>	on page 1: PDPCH has	been char	ged to DPCH
	<ul> <li>Section page 1°</li> </ul>	. •	about ESD	has been moved to Section 9 on
	<ul> <li>Table 4</li> </ul>	on page 2: I <sub>D</sub> value has	been adde	ed.
	<ul><li>Table 7</li></ul>	on page 3: PDPCH has	been char	ged to DPCH
	<ul> <li>Section</li> </ul>	7.2 on page 4: section	has been a	dded
	<ul><li>Figure</li></ul>	5 on page 5: redundant	conditions	about frequency have been removed
	<ul> <li>Table 9</li> </ul>	on page 8: title of table	has been o	hanged
	<ul> <li>Table 9</li> </ul>	on page 8: redundant ir	nformation	nas been removed
	<ul> <li>Section</li> </ul>	n 9 on page 11: section h	as been ac	lded.
BLF7G20L-250P_7G20LS-250P v.2	20100909	Preliminary data sheet	-	BLF7G20L-250P_7G20LS-250P v.1
BLF7G20L-250P_7G20LS-250P v.1	20091216	Objective data sheet	-	-

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#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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#### **Power LDMOS transistor**

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## **NXP Semiconductors**

**Power LDMOS transistor** 

## 14. Contents

1	Product profile
1.1	General description 1
1.2	Features and benefits
1.3	Applications
2	Pinning information 2
3	Ordering information 2
4	Limiting values
5	Thermal characteristics 3
6	Characteristics 3
7	Test information 3
7.1	Ruggedness in class-AB operation 3
7.2	Impedance information 4
7.3	Single carrier W-CDMA 5
7.4	One tone CW 6
7.5	2-carrier WCDMA characteristics 7
7.6	Test circuit
8	Package outline 9
9	Handling information 11
10	Abbreviations11
11	Revision history 12
12	Legal information
12.1	Data sheet status
12.2	Definitions
12.3	Disclaimers
12.4	Trademarks14
13	Contact information 14
14	Contents

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